

CMP180P04A/CMB180P04A/CMI180P04A

-40V, 4mΩ typ., -100A P-Channel MOSFET

General Description

The 180P04A is a P-channel Power MOSFET. They use advanced trench technology to provide excellent $R_{DS(ON)}$.

The device is therefore suitable in advanced high-efficiency switching applications.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
-40V	4.7mΩ	-100A

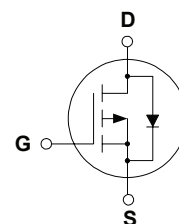
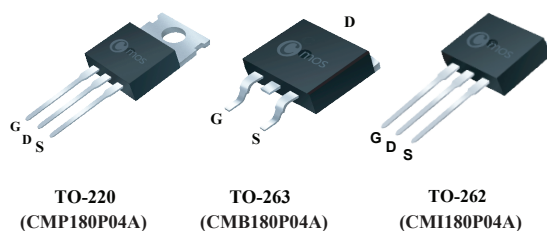
Applications

- DC-DC Converters
- Motor control
- LED controller

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-220/263/262 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	-100	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	-70	A
I_{DM}	Pulsed Drain Current	-400	A
EAS	Single Pulse Avalanche Energy (Note 1)	1250	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	136	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.92	°C/W

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-20A$	---	4	4.7	mΩ
		$V_{GS}=-4.5V$, $I_D=-20A$	---	4.8	6.0	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1	---	-3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	uA
		$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-20A$	---	47	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	9.2	---	Ω
Q_g	Total Gate Charge	$V_{DD}=-32V$, $I_D=-80A$ $V_{GS}=-10V$	---	200	---	nC
Q_{gs}	Gate-Source Charge		---	25	---	
Q_{gd}	Gate-Drain Charge		---	53	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-20V$, $V_{GS}=-10V$, $R_G=0\Omega$ $I_D=-40A$	---	35	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	245	---	
T_f	Fall Time		---	120	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	11500	---	pF
C_{oss}	Output Capacitance		---	770	---	
C_{rss}	Reverse Transfer Capacitance		---	670	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-100	A
I_{SM}	Pulsed Source Current		---	---	-400	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=-20A$	---	-0.78	-1.3	V

Notes:

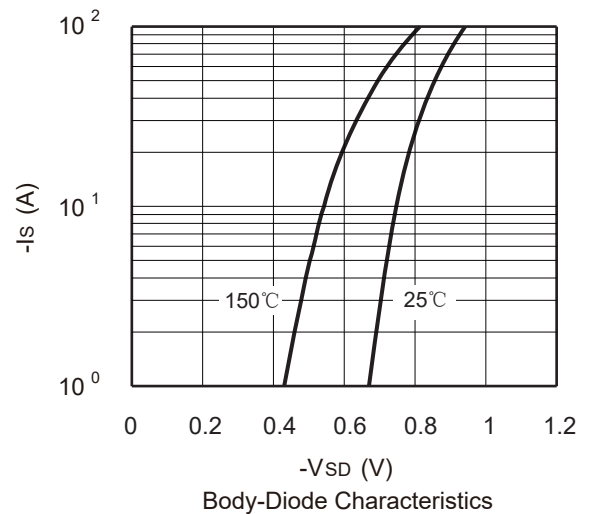
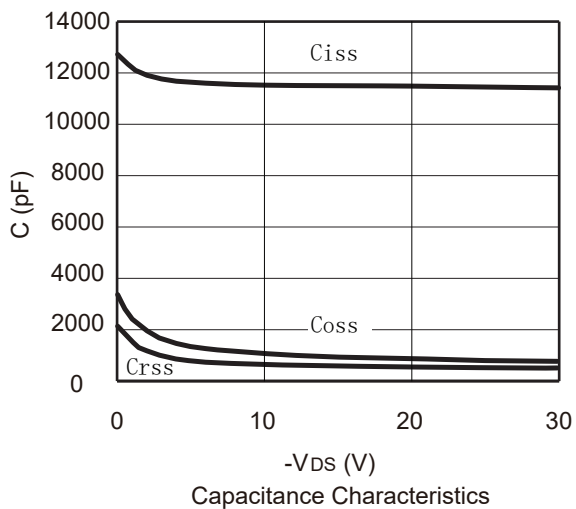
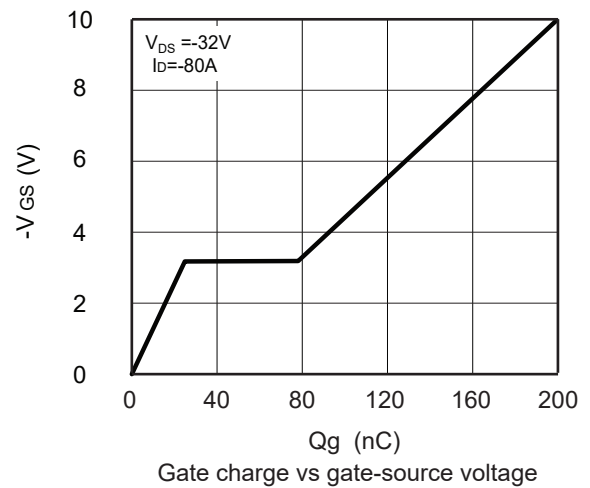
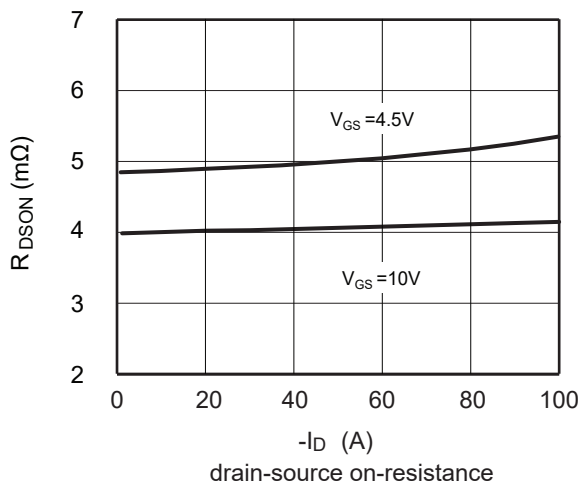
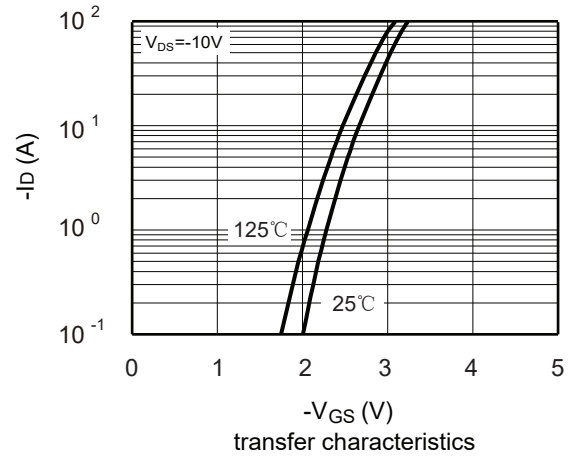
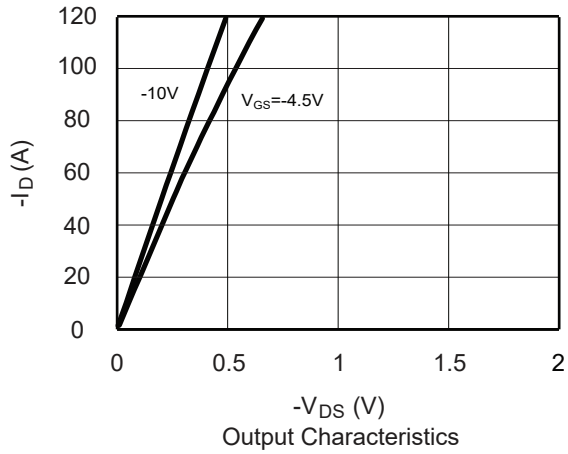
1.The EAS data shows Max. rating .The test condition is $V_{DS}=-30V$, $V_{GS}=-10V$, $L=1\text{mH}$, $I_{AS}=-50A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics



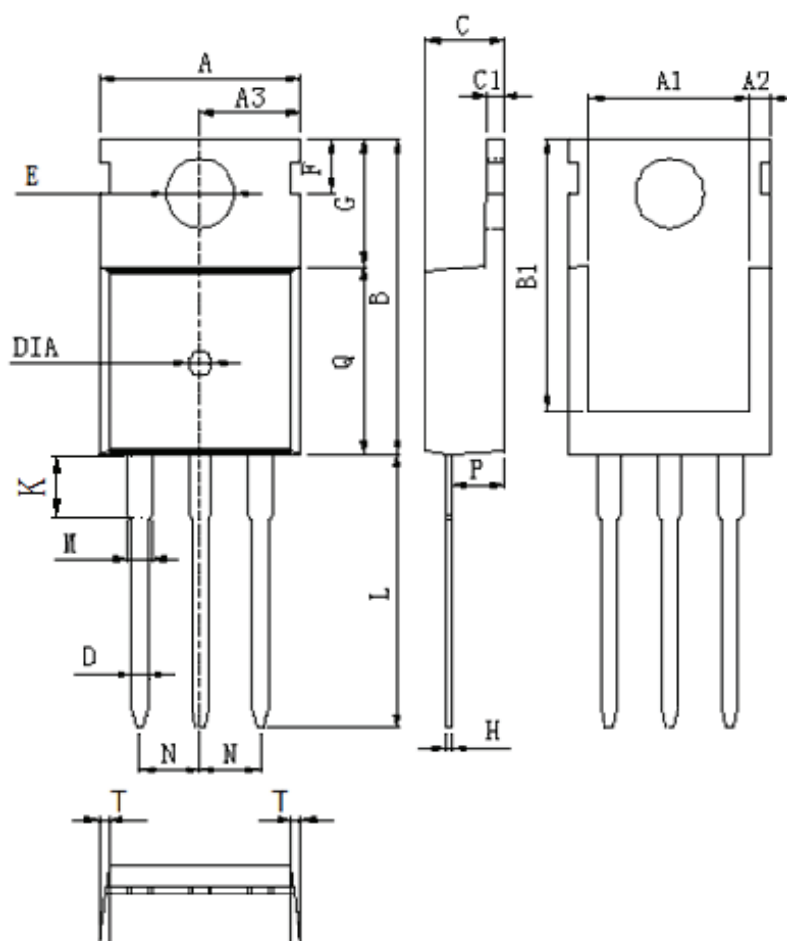
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Package Dimension

TO-220

Unit :mm



DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5 (deep 0.2)

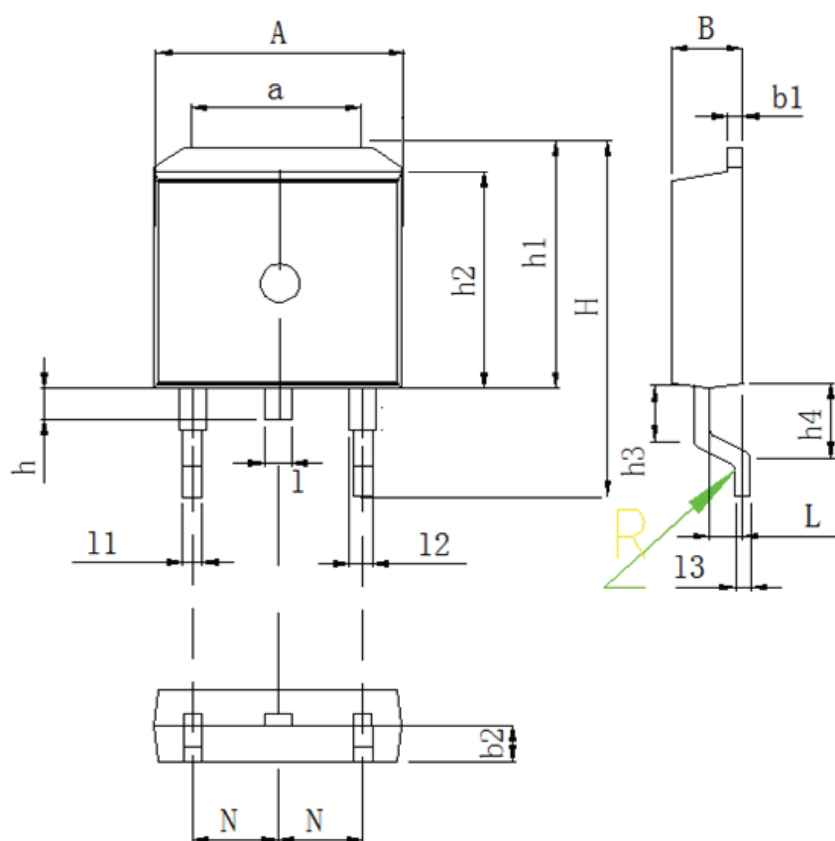
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Package Dimension

TO-263

Unit :mm



DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

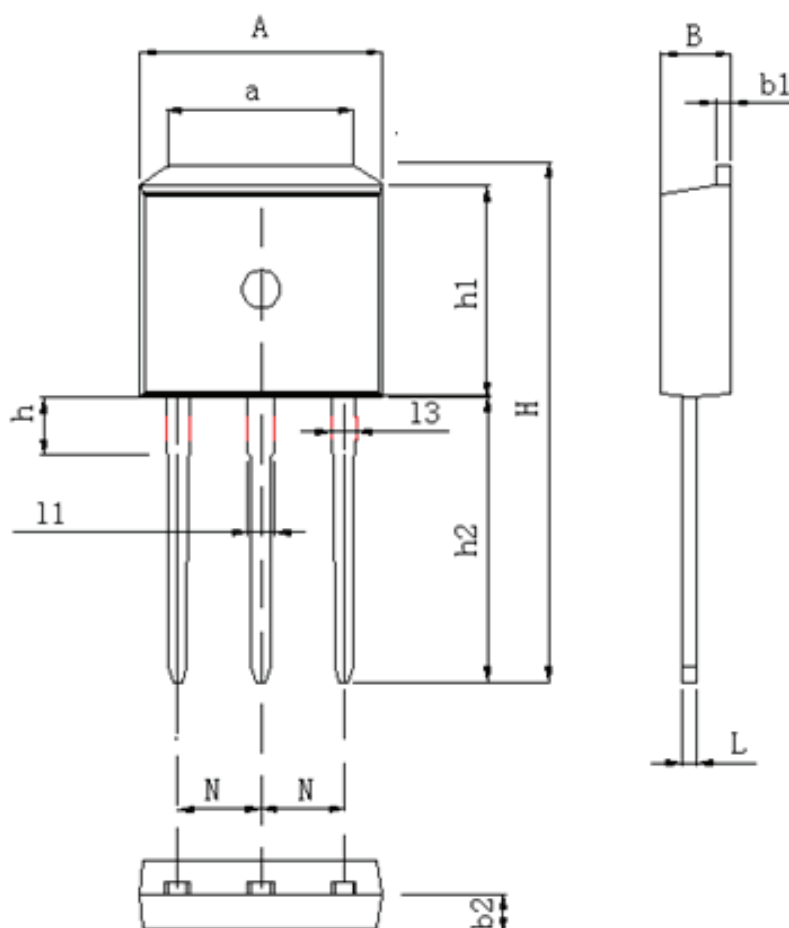
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Package Dimension

TO-262

Unit :mm



DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
l1	1.3 ± 0.1
l2	0.8 ± 0.1
N	2.45 ± 0.1